



DUAL PNP GENERAL PURPOSE SWITCHING TRANSISTOR

VOLTAGE 60 Volt POWER 150 mW

FEATURES

- PNP epitaxial silicon, planar design
- Collector-emitter voltage $V_{CE} = -60V$
- Collector current $I_{c} = -600 \text{mA}$
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. . (Halogen Free)

MECHANICAL DATA

· Case: SOT-363

• Terminals : Solderable per MIL-STD-750, Method 2026

• Apporx. Weight: 0.0002 ounces, 0.006 grams

• Marking: M7Q

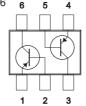
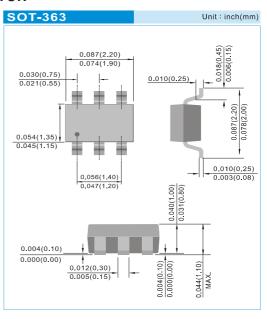


Fig.53



ABSOLUTE MAXIMUM RATINGS

Parameter		Value	Units	
Collector-Emitter Voltage	V _{CEO}	-60	٧	
Collector-Base Voltage	V _{CBO}	-60	٧	
Emitter-Base Voltage	V _{EBO}	-5.0	V	
Collector Current-Continuous	l _c	-600	mA	

THERMALCHATACTERISTICS

Parameter		Value	Units
Max Power Dissipation (Note 1)	P _{тот}	150	mW
Thermal Resistance, Junction to Ambient	R _{eJA}	830	°C / W
Storage Temperature	T _{stg}	-55 to +150	°C
Junction Temperaure	T _J	-55 to +150	°C

Note 1: Transistor mouted on FR-5 board 1.0 x 0.75 x 0.062 in.





ELECTRICAL CHARACTERISTICS (T_{,1}=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Тур.	Max.	Units
Collector-Emitter Breakdown Voltage	V _(BR) CEO	I _C =-10mA,I _B =0	-60	-	-	V
Collector-Base Breakdown Voltage	V _(BR) CBO	I _c =-10 A,I _E =0	-60	-	-	V
Emitter-Base Breakdown Voltage	V _(BR) EBO	I _E =-10 A,I _C =0	-5.0	-	-	V
Base Cutoff Current	I _{BL}	V _{CE} =-30V,V _{EB} =-0.5V	-	-	-50	nA
Collector Cutoff Current	I _{CEX}	V _{CE} =-30V,V _{EB} =-0.5V	-	-	-50	nA
		V _{CB} =-50V,I _E =0	-	-	-10	nA
	Г _{сво}	V _{CB} =-50V,I _E =0 T _J =125°C	-	-	-10	А
DC Current Gain	h _{FE}	$\begin{array}{c} I_{c} \!\!=\!\! -0.1 \text{mA}, V_{cE} \!\!=\!\! -10 \text{V} \\ I_{c} \!\!=\!\! -1.0 \text{mA}, V_{cE} \!\!=\!\! -10 \text{V} \\ I_{c} \!\!=\!\! -10 \text{mA}, V_{cE} \!\!=\!\! -10 \text{V} \\ I_{c} \!\!=\!\! -150 \text{mA}, V_{cE} \!\!=\!\! -10 \text{V} \\ I_{c} \!\!=\!\! -500 \text{mA}, V_{cE} \!\!=\!\! -10 \text{V} \end{array}$	75 100 100 100 50	- - - -	- - - 300 -	-
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _c =-150mA,I _B =-15mA I _c =-500mA,I _B =-50mA	-	-	-0.4 -1.6	٧
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-150mA,I _B =-15mA I _C =-500mA,I _B =-50mA	-	-	-1.3 -2.6	٧
Collector-Base Capacitance	C _{CBO}	V _{CB} =-10V,I _E =0,f=1MHz	-	-	8.0	pF
Emitter-Base Capacitance	C _{EBO}	V _{CB} =-2V,I _C =0,f=1MHz	-	-	30	pF
Current Gain-Bandwidth Product	F _T	I _c =-50mA,V _{ce} =-20V, f=100MHz	200	-	-	MHz
Turn-On Time	t _{on}	V _{cc} =-30V,V _{BE} =-0.5V, I _c =-150mA,I _B =-15mA	-	-	45	ns
Delay Time	t _d	V _{cc} =-30V,V _{BE} =-0.5V, I _c =-150mA,I _B =-15mA	-	-	20	ns
Rise Time	t _r	V _{CC} =-30V,V _{BE} =-0.5V, I _C =-150mA,I _{B1} =-15mA	-	-	40	ns
Turn-Off Time	t _{off}	V _{cc} =-6V,I _c =-150mA, I _{B1} =I _{B2} =-15mA	-	-	250	ns
Storage Time	t _s	V _{cc} =-6V,I _c =-150mA, I _{B1} =I _{B2} =-15mA	-	-	230	ns
Fall Time	t _f	V _{cc} =-6V,I _c =-150mA, I _{B1} =I _{B2} =-15mA	-	-	30	ns





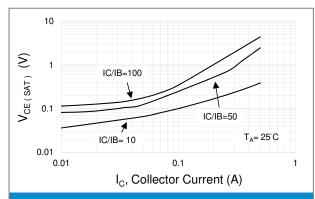


Fig.1 Typical Collector-Emitter Saturation Voltage

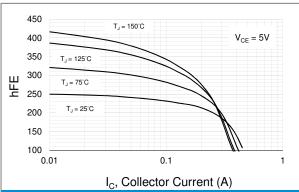


Fig.3 Typical DC Current Gain vs Collector Current

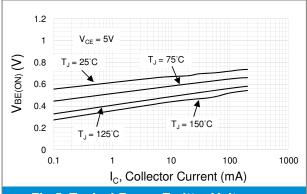


Fig.5 Typical Base - Emitter Voltage vs **Collector Current**

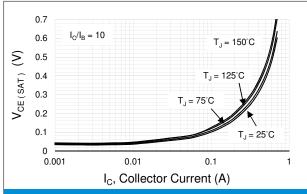


Fig.2 Typical Collector-Emitter Saturation Voltage

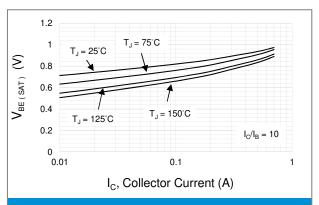


Fig.4 Typical Base-Emitter Saturation Voltage

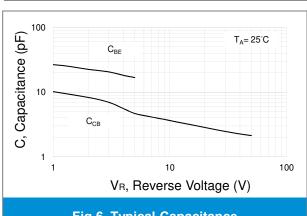


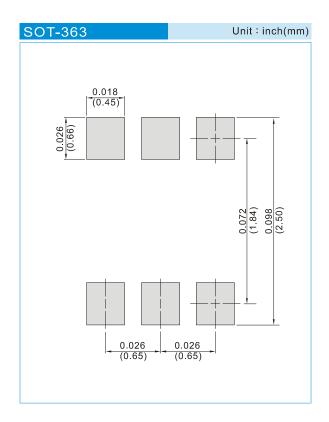
Fig.6 Typical Capacitance

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MOUNTING PAD LAYOUT



ORDER INFORMATION

· Packing information

T/R - 10K per 13" plastic Reel

T/R - 3K per 7" plastic Reel

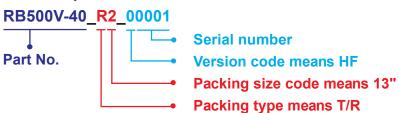




Part No_packing code_Version

MMDT2907AQ_R1_00001 MMDT2907AQ_R2_00001

For example:



Packing Code XX			Version Code XXXXX			
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1 st Code	2 nd ~5 th Code
Tape and Ammunition Box (T/B)	A	N/A	0	HF	0	serial number
Tape and Reel (T/R)	R	7"	1	RoHS	1	serial number
Bulk Packing (B/P)	В	13"	2			
Tube Packing (T/P)	Т	26mm	X			
Tape and Reel (Right Oriented) (TRR)	S	52mm	Y			
Tape and Reel (Left Oriented) (TRL)	L	PANASERT T/B CATHODE UP (PBCU)	U			
FORMING	F	PANASERT T/B CATHODE DOWN (PBCD)	D			





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